

Advanced VLSI Design

Lecture 12: Combinational Circuits

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Adapted from lecture notes from Rutgers university

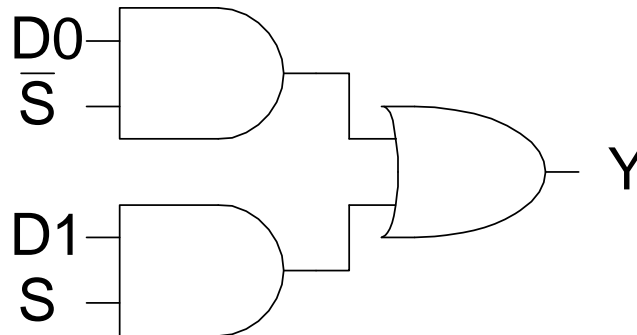
Outline

- Bubble Pushing
- Compound Gates
- Logical Effort Example
- Input Ordering
- Asymmetric Gates
- Skewed Gates
- Best P/N ratio

Example 1

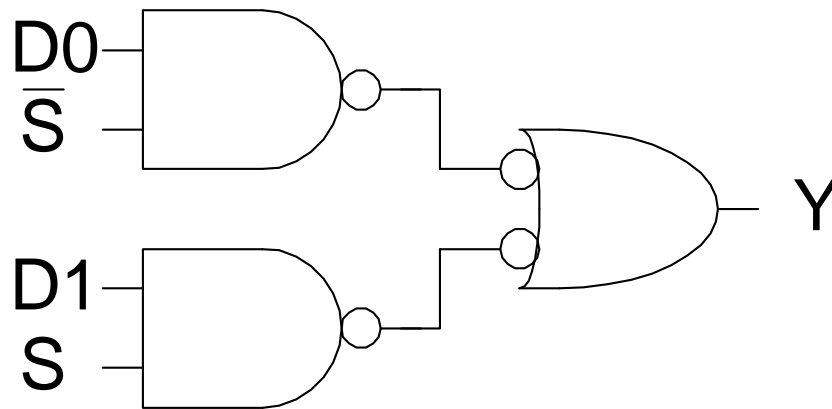
```
module mux(input s, d0, d1,  
           output y);  
  
    assign y = s ? d1 : d0;  
endmodule
```

1) Sketch a design using AND, OR, and NOT gates.



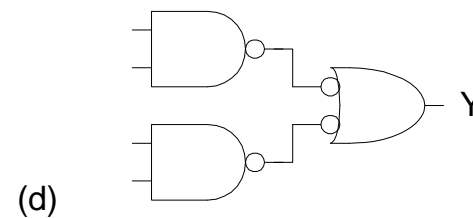
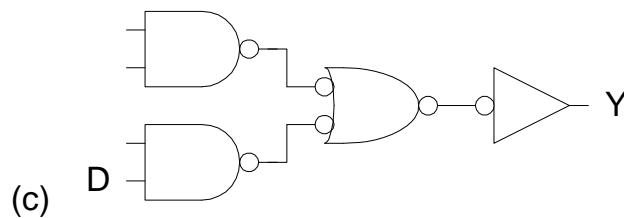
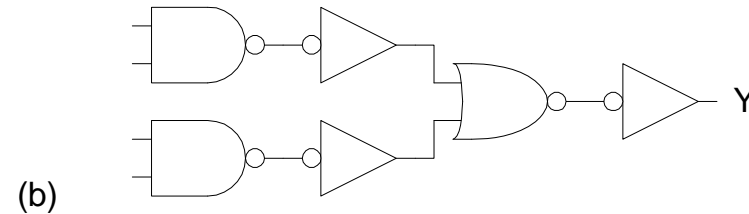
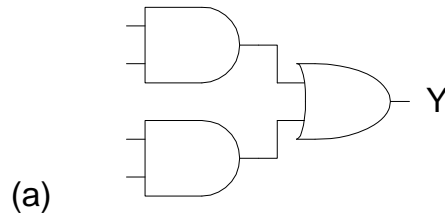
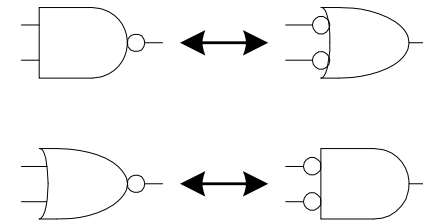
Example 2

2) Sketch a design using NAND, NOR, and NOT gates.
Assume $\sim S$ is available.



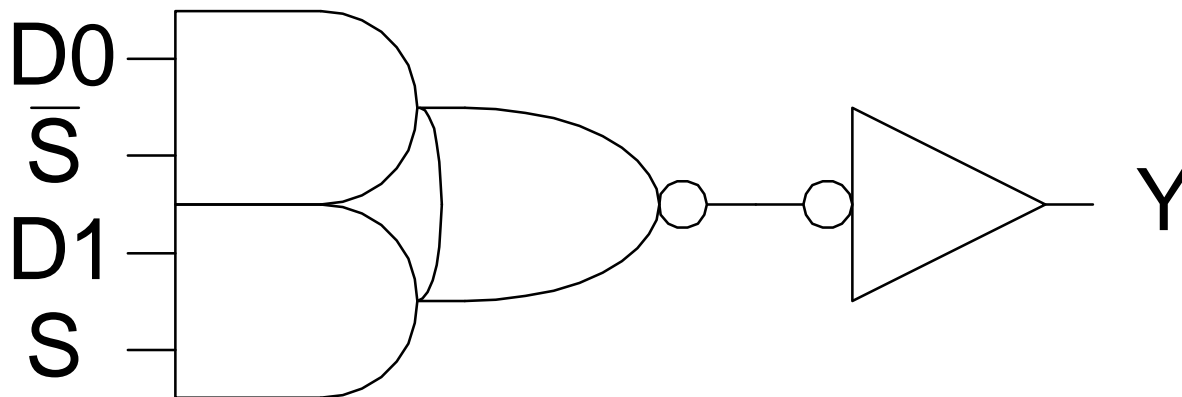
Bubble Pushing

- ❑ Start with network of AND / OR gates
- ❑ Convert to NAND / NOR + inverters
- ❑ Push bubbles around to simplify logic
 - Remember DeMorgan's Law



Example 3

- 3) Sketch a design using one compound gate and one NOT gate. Assume $\sim S$ is available.

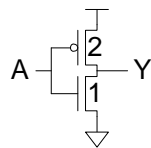
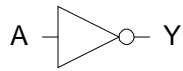


Compound Gates

□ Logical Effort of compound gates

unit inverter

$$Y = \overline{A}$$

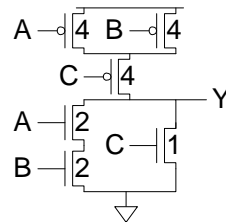
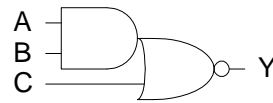


$$g_A = 3/3$$

$$p = 3/3$$

AOI21

$$Y = \overline{A \square B + C}$$



$$g_A = 6/3$$

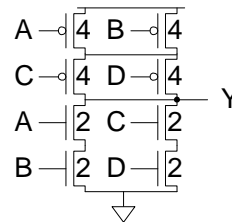
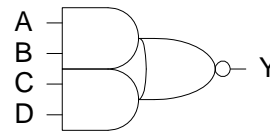
$$g_B = 6/3$$

$$g_C = 5/3$$

$$p = 7/3$$

AOI22

$$Y = \overline{A \square B + C \square D}$$



$$g_A =$$

$$g_B =$$

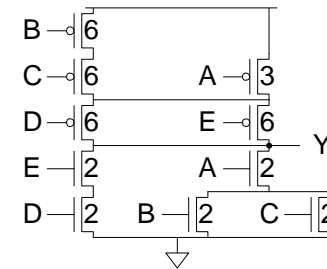
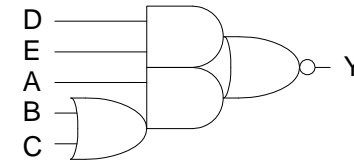
$$g_C =$$

$$g_D =$$

$$p =$$

Complex AOI

$$Y = \overline{A \square (B + C) + D \square E}$$



$$g_A =$$

$$g_B =$$

$$g_C =$$

$$g_D =$$

$$g_E =$$

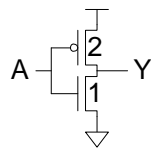
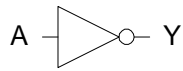
$$p =$$

Compound Gates

□ Logical Effort of compound gates

unit inverter

$$Y = \overline{A}$$

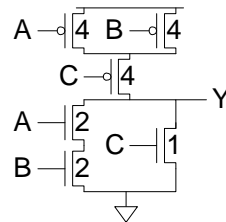
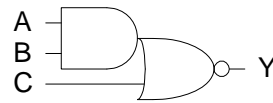


$$g_A = 3/3$$

$$p = 3/3$$

AOI21

$$Y = \overline{A \square B + C}$$



$$g_A = 6/3$$

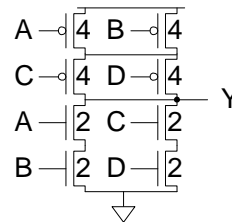
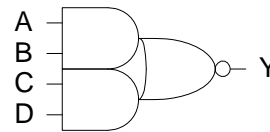
$$g_B = 6/3$$

$$g_C = 5/3$$

$$p = 7/3$$

AOI22

$$Y = \overline{A \square B + C \square D}$$



$$g_A = 6/3$$

$$g_B = 6/3$$

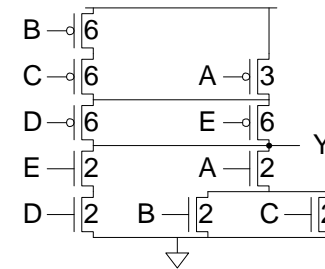
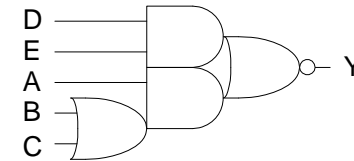
$$g_C = 6/3$$

$$g_D = 6/3$$

$$p = 12/3$$

Complex AOI

$$Y = \overline{A \square (B + C) + D \square E}$$



$$g_A = 5/3$$

$$g_B = 8/3$$

$$g_C = 8/3$$

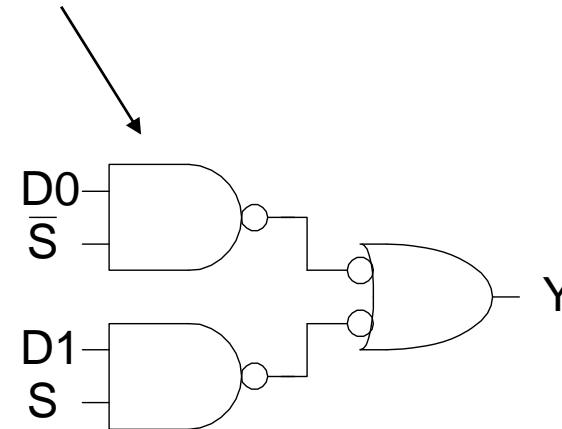
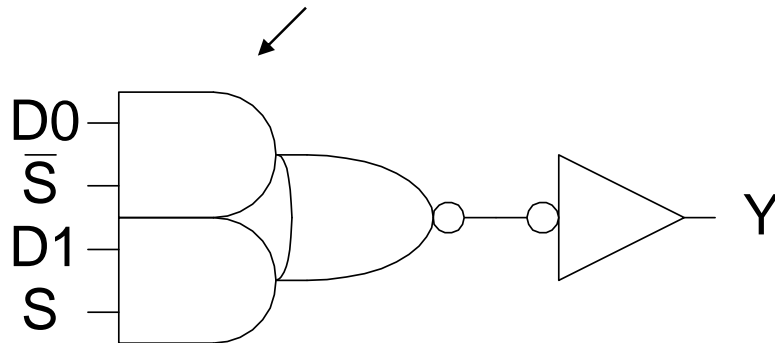
$$g_D = 8/3$$

$$g_E = 8/3$$

$$p = 16/3$$

Example 4

- The multiplexer has a maximum input capacitance of 16 units on each input. It must drive a load of 160 units. Estimate the delay of the NAND and compound gate designs.



$$H = 160 / 16 = 10$$

$$B = 1$$

$$N = 2$$

NAND Solution

$$P = 2 + 2 = 4$$

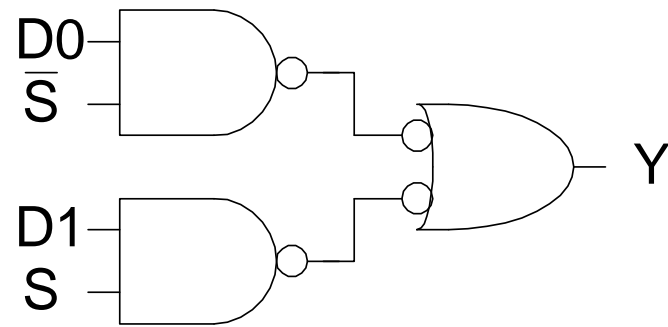
$$G = (4/3) \cdot (4/3) = 16/9$$

$$F = GBH = 160/9$$

$$f = \sqrt[4]{F} = 4.2$$

^

$$D = N f + P = 12.4\tau$$



Compound Solution

$$P = 4 + 1 = 5$$

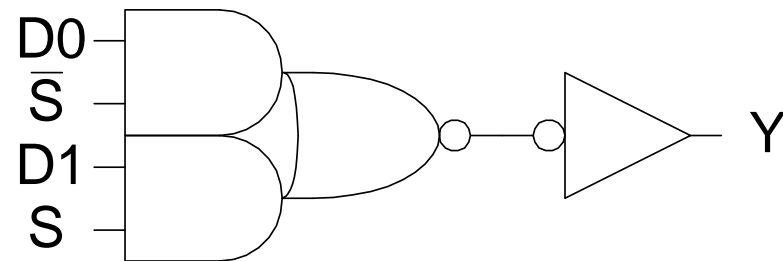
$$G = (6 / 3) \bullet (1) = 2$$

$$F = GBH = 20$$

$$f = \sqrt[N]{F} = 4.5$$

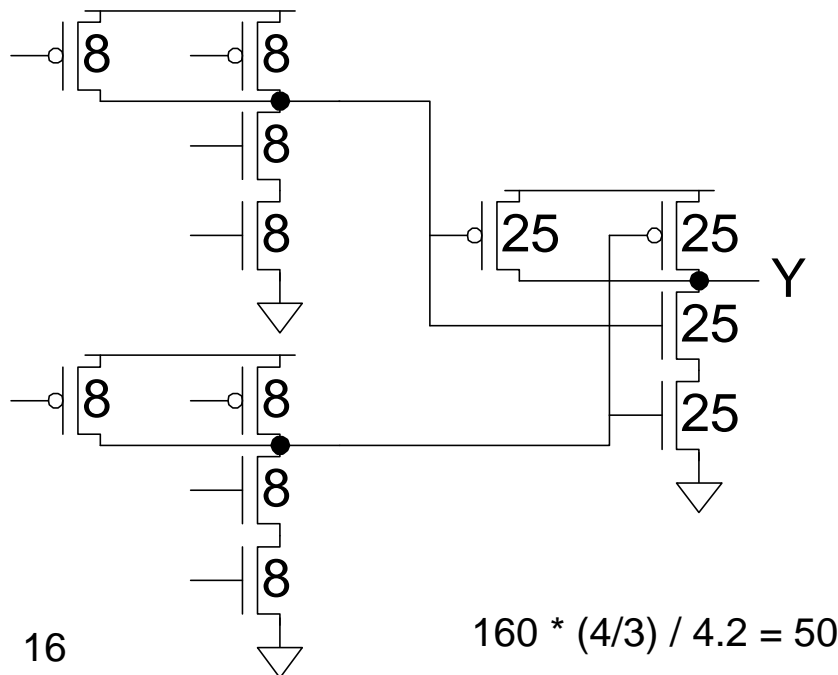
^

$$D = N f + P = 14\tau$$



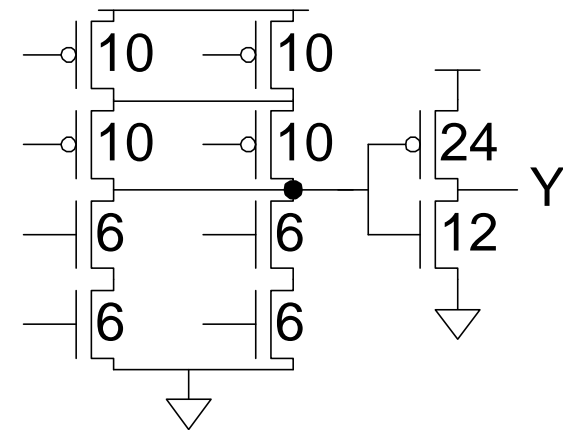
Example 5

- Annotate your designs with transistor sizes that achieve this delay.



16

$$160 * (4/3) / 4.2 = 50$$

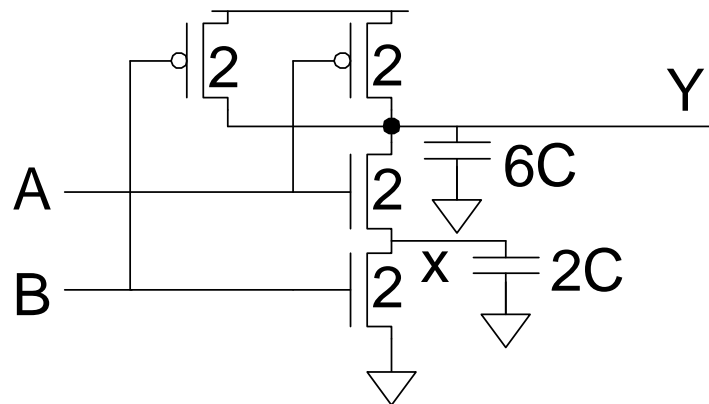


16

$$160 * 1 / 4.5 = 36$$

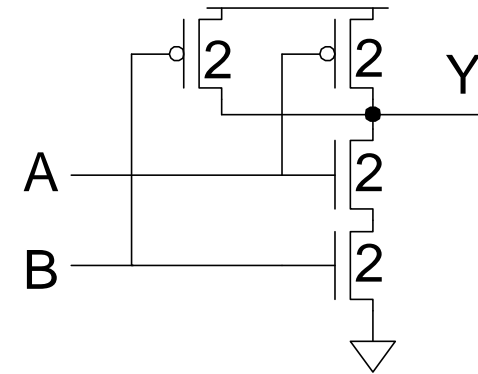
Input Order

- Our parasitic delay model was too simple
 - Calculate parasitic delay for Y falling
 - If A arrives latest? $6RC$ (2τ)
 - If B arrives latest? $6RC + RC = 7RC$ (2.33τ)



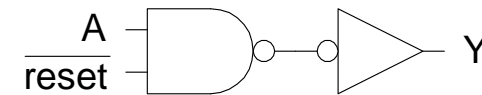
Inner & Outer Inputs

- ❑ *Outer* input is closest to rail (B)
- ❑ *Inner* input is closest to output (A)
- ❑ If input arrival time is known
 - Connect latest input to inner terminal

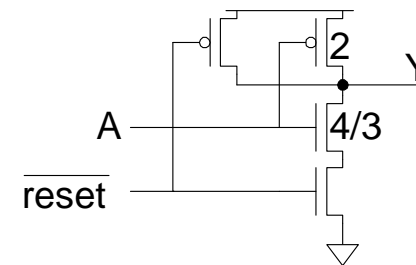


Asymmetric Gates

- ❑ Asymmetric gates favor one input over another
- ❑ Ex : suppose input A of a NAND gate is most critical
 - Use smaller transistor on A (less capacitance)
 - Boost size of noncritical input
 - So total resistance is same

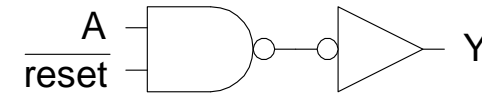


- ❑ $g_A =$
- ❑ $g_B =$
- ❑ $g_{total} = g_A + g_B =$
- ❑ Asymmetric gate approaches $g = 1$ on critical input
- ❑ But total logical effort goes up

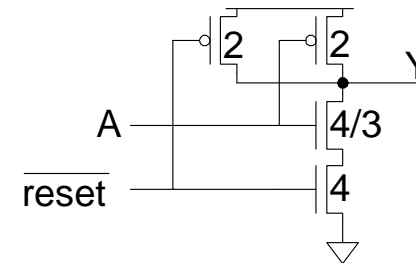


Asymmetric Gates

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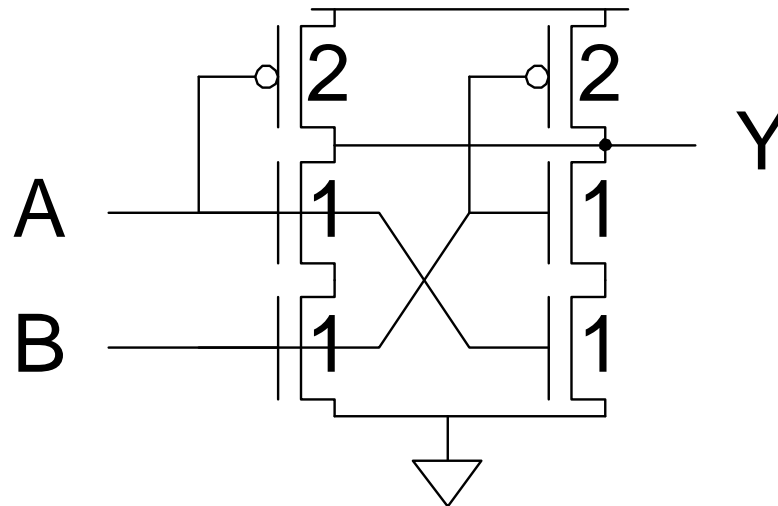


- ❑ $g_A = 10/9$
- ❑ $g_B = 2$
- ❑ $g_{\text{total}} = g_A + g_B = 28/9$
- ❑ Asymmetric gate approaches $g = 1$ on critical input
- ❑ But total logical effort goes up



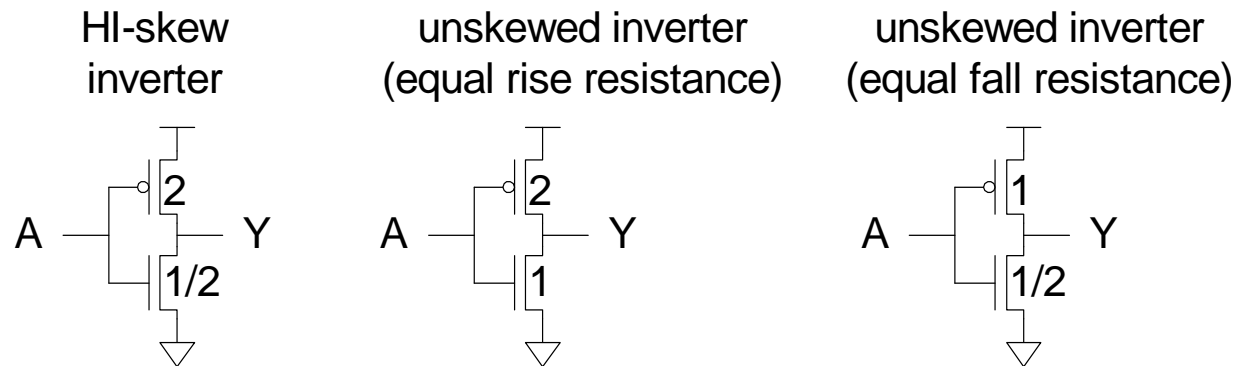
Symmetric Gates

- Inputs can be made perfectly symmetric



Skewed Gates

- ❑ Skewed gates favor one edge over another
- ❑ Ex: suppose rising output of inverter is most critical
 - Downsize noncritical nMOS transistor

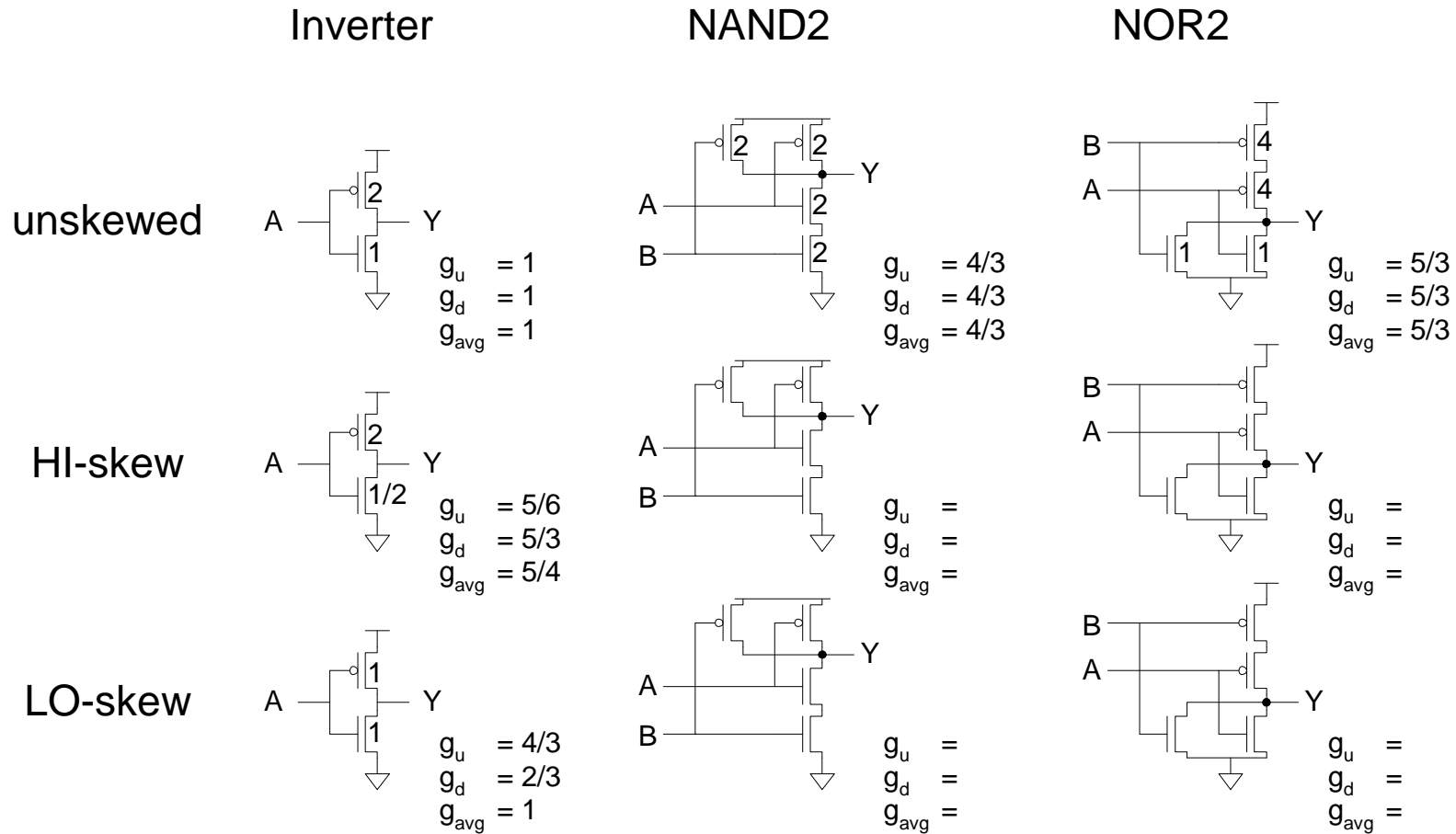


- ❑ Calculate logical effort by comparing to unskewed inverter with same effective resistance on that edge.
 - $g_u = 2.5 / 3 = 5/6$
 - $g_d = 2.5 / 1.5 = 5/3$

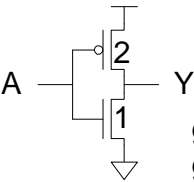
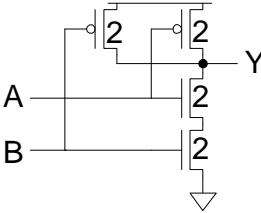
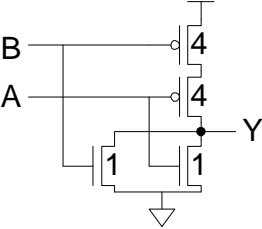
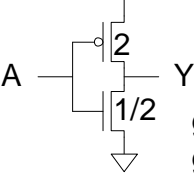
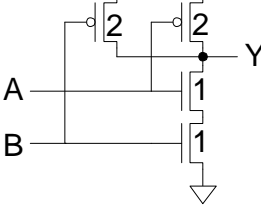
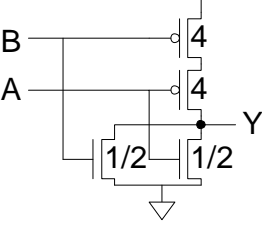
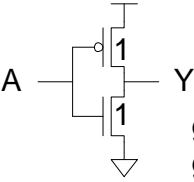
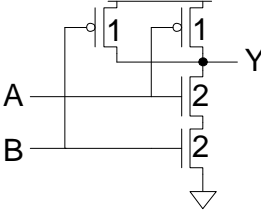
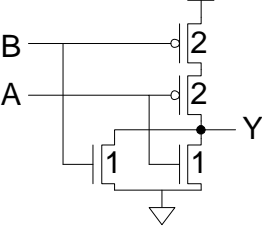
HI- and LO-Skew

- ❑ Definition: Logical effort of a skewed gate for a particular transition is the ratio of the input capacitance of that gate to the input capacitance of an unskewed inverter delivering the same output current for the same transition.
- ❑ Skewed gates reduce size of noncritical transistors
 - HI-skew gates favor rising output (small nMOS)
 - LO-skew gates favor falling output (small pMOS)
- ❑ Logical effort is smaller for favored direction
- ❑ But larger for the other direction

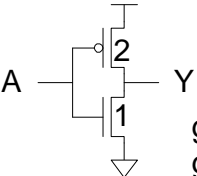
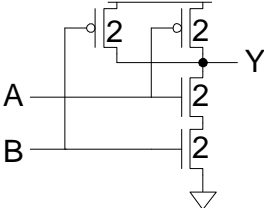
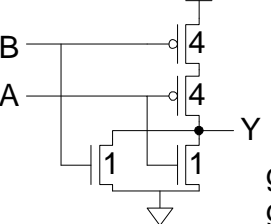
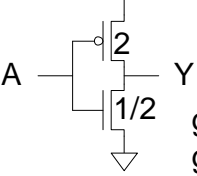
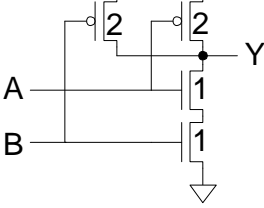
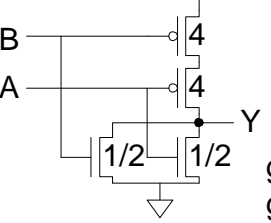
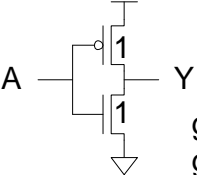
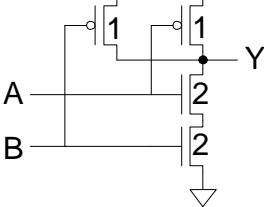
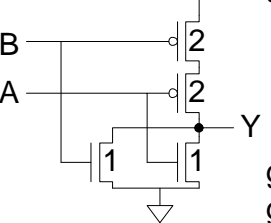
Catalog of Skewed Gates



Catalog of Skewed Gates

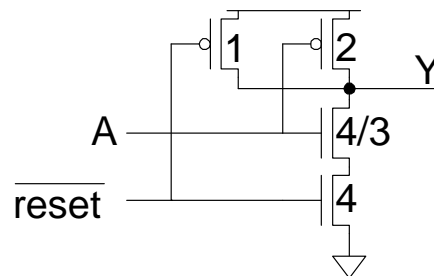
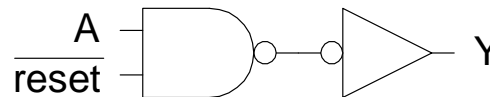
	Inverter	NAND2	NOR2
unskewed	 $g_u = 1$ $g_d = 1$ $g_{avg} = 1$	 $g_u = 4/3$ $g_d = 4/3$ $g_{avg} = 4/3$	 $g_u = 5/3$ $g_d = 5/3$ $g_{avg} = 5/3$
HI-skew	 $g_u = 5/6$ $g_d = 5/3$ $g_{avg} = 5/4$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$
LO-skew	 $g_u = 4/3$ $g_d = 2/3$ $g_{avg} = 1$	 $g_u =$ $g_d =$ $g_{avg} =$	 $g_u =$ $g_d =$ $g_{avg} =$

Catalog of Skewed Gates

	Inverter	NAND2	NOR2
unskewed	 $g_u = 1$ $g_d = 1$ $g_{avg} = 1$	 $g_u = 4/3$ $g_d = 4/3$ $g_{avg} = 4/3$	 $g_u = 5/3$ $g_d = 5/3$ $g_{avg} = 5/3$
HI-skew	 $g_u = 5/6$ $g_d = 5/3$ $g_{avg} = 5/4$	 $g_u = 1$ $g_d = 2$ $g_{avg} = 3/2$	 $g_u = 3/2$ $g_d = 3$ $g_{avg} = 9/4$
LO-skew	 $g_u = 4/3$ $g_d = 2/3$ $g_{avg} = 1$	 $g_u = 2$ $g_d = 1$ $g_{avg} = 3/2$	 $g_u = 2$ $g_d = 1$ $g_{avg} = 3/2$

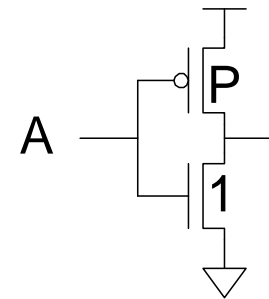
Asymmetric Skew

- Combine asymmetric and skewed gates
 - Downsize noncritical transistor on unimportant input
 - Reduces parasitic delay for critical input



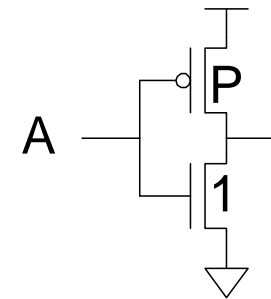
Best p/n Ratio

- ❑ We have selected p/n ratio for unit rise and fall resistance ($\mu = 2-3$ for an inverter).
- ❑ Alternative: choose ratio for least average delay
- ❑ Ex: inverter
 - Delay driving identical inverter
 - $t_{pdf} =$
 - $t_{pdr} =$
 - $t_{pd} =$
 - Differentiate t_{pd} w.r.t. P
 - Least delay for $P =$



Best p/n Ratio

- ❑ We have selected p/n ratio for unit rise and fall resistance ($\mu = 2-3$ for an inverter).
- ❑ Alternative: choose ratio for least average delay
- ❑ Ex: inverter
 - Delay driving identical inverter
 - $t_{pdf} = (P+1)$
 - $t_{pdr} = (P+1)(\mu/P)$
 - $t_{pd} = (P+1)(1+\mu/P)/2 = (P + 1 + \mu + \mu/P)/2$
 - Differentiate t_{pd} w.r.t. P
 - Least delay for $P = \sqrt{\mu}$

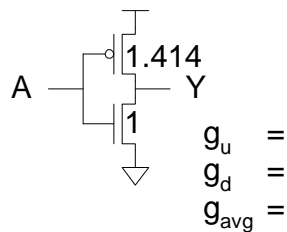


p/n Ratios

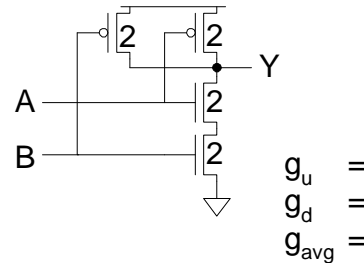
- In general, best p/n ratio is sqrt of equal delay ratio.
 - Only improves average delay slightly for inverters
 - But significantly decreases area and power

Inverter

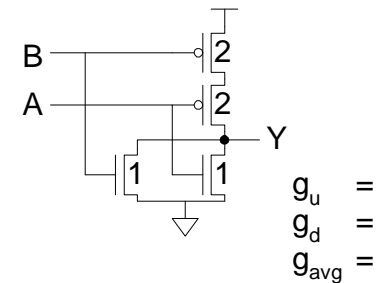
fastest
P/N ratio



NAND2



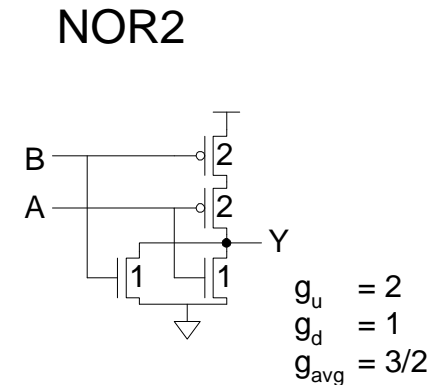
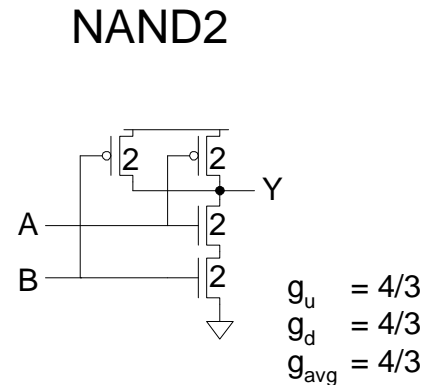
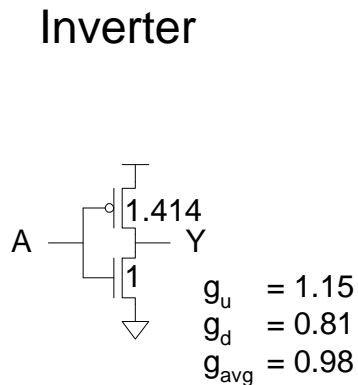
NOR2



p/n Ratios

- In general, best p/n ratio is sqrt of equal delay ratio.
 - Only improves average delay slightly for inverters
 - But significantly decreases area and power
 - May degrade noise margin

fastest
P/N ratio



Observations

- ❑ For speed:
 - NAND vs. NOR
 - Many simple stages vs. fewer high fan-in stages
 - Latest-arriving input
- ❑ For area and power:
 - Many simple stages vs. fewer high fan-in stages